UNISONIC TECHNOLOGIES CO., LTD

05N60-CB **Preliminary Power MOSFET**

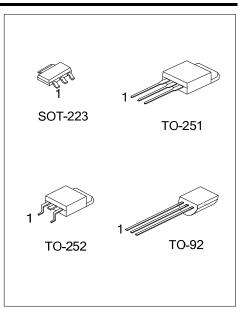
0.5A, 600V **N-CHANNEL POWER MOSFET**

DESCRIPTION

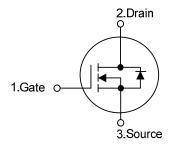
The UTC 05N60-CB is a high voltage MOSFET and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and have a high rugged avalanche characteristics. This power MOSFET is usually used at high speed switching applications in power supplies, PWM motor controls, high efficient DC to DC converters and bridge circuits.

FEATURES

- * $R_{DS(ON)}$ < 23 Ω @ V_{GS} = 10V, I_{D} = 0.25A
- * Fast switching capability
- * Avalanche energy specified
- * Improved dv/dt capability, high ruggedness



SYMBOL



ORDERING INFORMATION

Ordering Number		Dookogo	Pin Assignment			Dooking	
Lead Free	Halogen Free	Package	1 2		3	Packing	
-	05N60G-AA3-R	SOT-223	G	D	S	Tape Reel	
05N60L-TM3-T	05N60G-TM3-T	TO-251	G	D	S	Tube	
05N60L-TN3-R	05N60G-TN3-R	TO-252	G	D	S	Tape Reel	
05N60L-T92-B	05N60G-T92-B	TO-92	G	D	S	Tape Box	
05N60L-T92-K	05N60G-T92-K	TO-92	G	D	S	Bulk	

Pin Assignment: G: Gate D: Drain S: Source



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MARKING

PACKAGE	MARKING
SOT-223	05N60G Lot Code Data Code 1
TO-251 / TO-252	UTC 05N60 G: Halogen Free Lot Code Data Code
TO-92	UTC 05N60□ L: Lead Free G: Halogen Free Lot Code → Data Code



ABSOLUTE MAXIMUM RATINGS (T_C = 25°C, unless otherwise specified.)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	600	V
Gate-Source Voltage		V_{GSS}	±30	V
Continuous Drain Current		I_{D}	0.5	Α
Pulsed Drain Current (No	ote 2)	I_{DM}	2	Α
Avalanche Energy	Single Pulse(Note 3)	E _{AS}	25	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/ dt	4.5	V/ns
	SOT-223		6	W
Power Dissipation	TO-251/TO-252	P_{D}	27	W
	TO-92		1.4	W
Junction Temperature		TJ	+150	°C
Storage Temperature		T_{STG}	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

- 2. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 3. L=150mH, I_{AS} =0.5A, V_{DD} =50V, R_{G} =0 Ω , Starting T_{J} =25°C
- 4. $I_{SD} \le 1.0A$, di/dt $\le 200A/\mu s$, $V_{DD} \le BV_{DSS}$, Starting $T_J = 25^{\circ}C$

THERMAL DATA

PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient	SOT-223		150	°C/W
	TO-251/TO-252	θ_{JA}	110	°C/W
	TO-92		160	°C/W
Junction to Case	SOT-223		20	°C/W
	TO-251/TO-252	θЈС	4.63	°C/W
	TO-92		88	°C/W



ELECTRICAL CHARACTERISTICS (T_J =25°C, unless otherwise specified.)

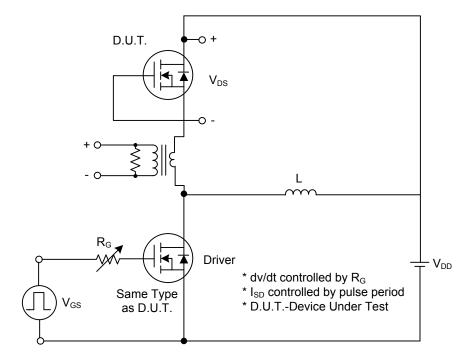
PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS		- · · · · - 					, ,,,,,
Drain-Source Breakdown Voltage		BV _{DSS}	$V_{GS} = 0V, I_D = 250\mu A$	600			V
Drain-Source Leakage Current (T _J =25°C)		I _{DSS}	V _{DS} = 600V, V _{GS} = 0V			10	
Drain-Source Leakage Current (T _J =125°C)						10	μA
Gate-Source Leakage Current	Forward	I _{GSS}	V _{GS} = 30V, V _{DS} = 0V			100	nA
	Reverse		V _{GS} = -30V, V _{DS} = 0V			-100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage		$V_{GS(TH)}$	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	2.0		4.0	V
Static Drain-Source On-State Resist	ance	R _{DS(ON)}	$V_{GS} = 10V, I_D = 0.25A$			23	Ω
DYNAMIC CHARACTERISTICS							
Input Capacitance		C_{ISS}			87		pF
Output Capacitance		Coss	V _{DS} =25V, V _{GS} =0V, f=1MHz		12		pF
Reverse Transfer Capacitance		C_{RSS}			5		pF
SWITCHING CHARACTERISTICS							
Total Gate Charge (Note 1)		Q_G	\/ -E0\/ \/ -10\/ -1.3A		7.0		nC
Gate-Source Charge		Q_GS	V_{DS} =50V, V_{GS} =10V, I_{D} =1.3A, I_{G} = 100 μ A (Note 1, 2)		1.0		nC
Gate-Drain Charge		Q_{GD}	ig = 100μΑ (Note 1, 2)		0.5		nC
Turn-On Delay Time (Note 1)		t _{D (ON)}			18		ns
Turn-On Rise Time		t _R	V _{DD} =30V, V _{GS} =10V,		16		ns
Turn-Off Delay Time		t _{D (OFF)}	$I_D = 0.5A, R_G = 25\Omega \text{ (Note 1, 2)}$		38		ns
Turn-Off Fall Time		t_{F}			28		ns
SOURCE- DRAIN DIODE RATINGS	S AND CHA	RACTERIS	rics				
Maximum Continuous Drain-Source	Diode	l.				1.0	Α
Forward Current		I _S	IS			1.0	
Maximum Pulsed Drain-Source Diode Forward		I _{SM}				4.0	Α
Current						4.0	^
Drain-Source Diode Forward Voltage (Note 1)		V_{SD}	V_{GS} =0V, I_{SD} = 0.5A			1.6	V
Reverse Recovery Time (Note 1)		t _{rr}	V_{GS} =0V, I_{SD} = 1.0A		375		ns
Reverse Recovery Charge		Q_{rr}	di/dt = 100A/μs		0.4		μC

Notes: 1. Pulse Test: Pulse Width≤300µs, Duty Cycle≤2%

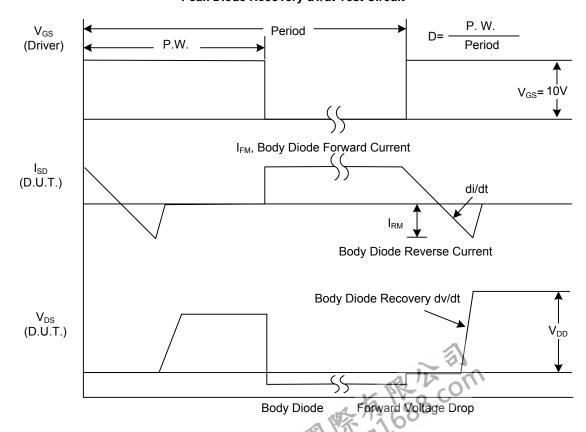


^{2.} Essentially independent of operating temperature.

TEST CIRCUITS AND WAVEFORMS

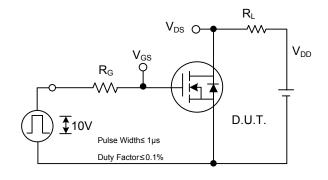


Peak Diode Recovery dv/dt Test Circuit



Peak Diode Recovery dv/dt Waveforms

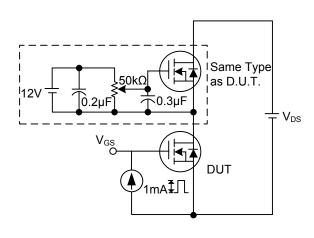
TEST CIRCUITS AND WAVEFORMS (Cont.)

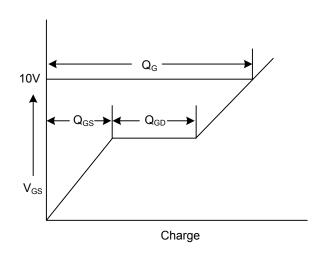


 $V_{\text{DS}} \\$ 90%

Switching Test Circuit

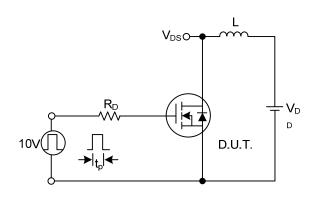
Switching Waveforms

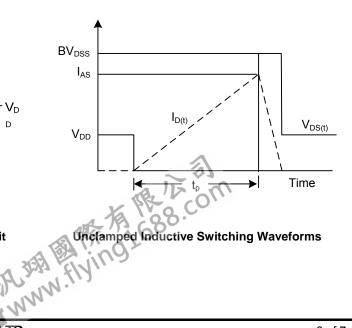




Gate Charge Test Circuit

Gate Charge Waveform





Unclamped Inductive Switching Test Circuit

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